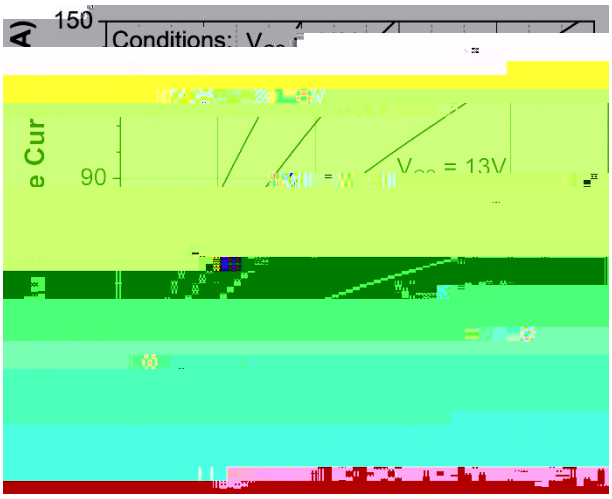
				≤	

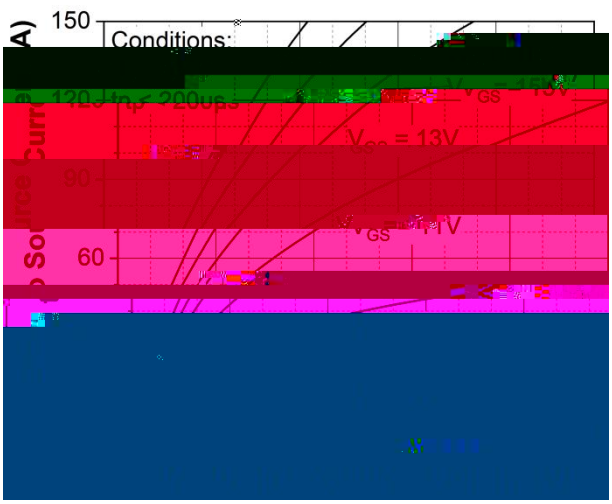


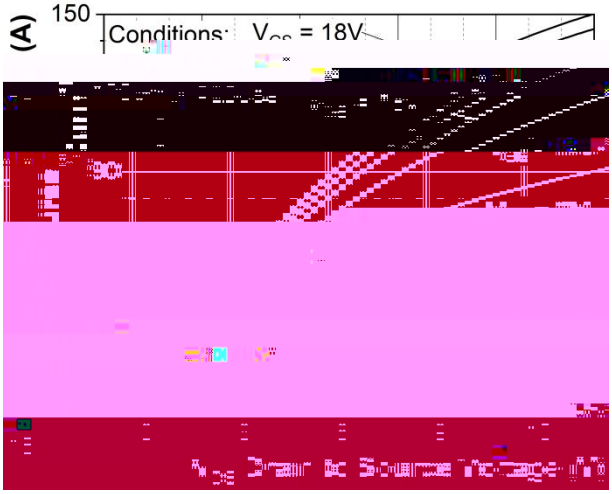


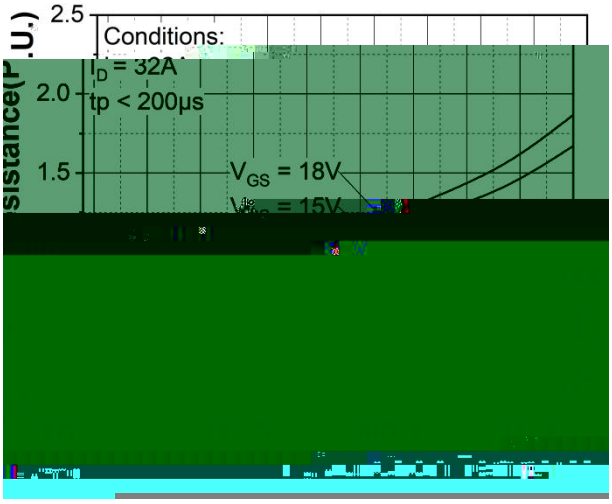
•%C•

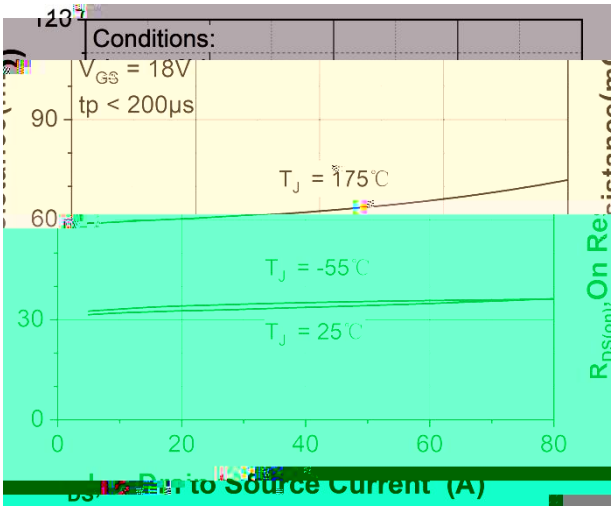
%K Ÿ P U e,Bp d •

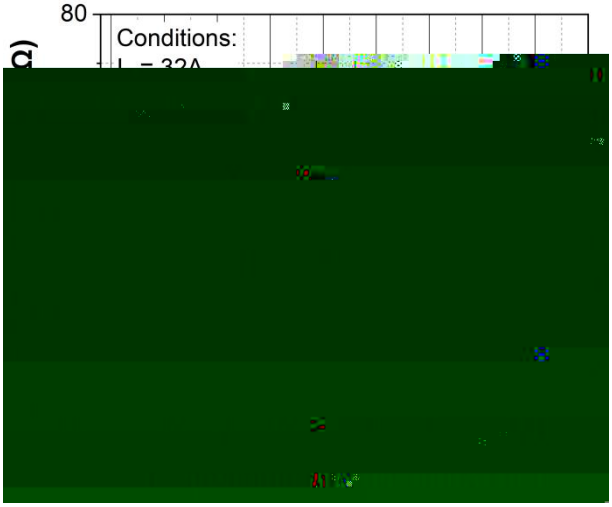

150
Conditions:
90
V_{GS} = 13V

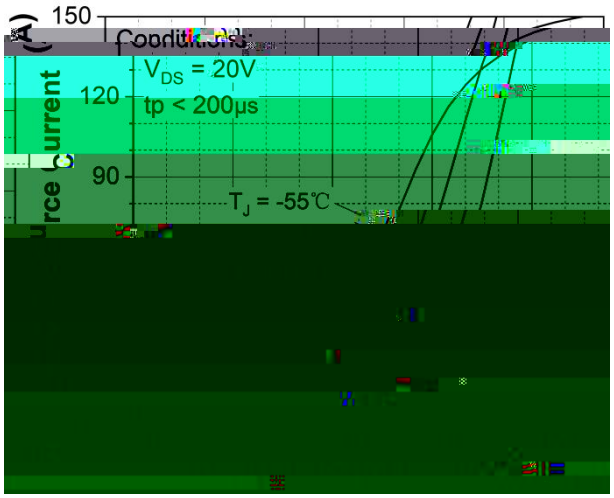

150
Conditions:
120
tp < 200μs
V_{GS} = 13V
90
60

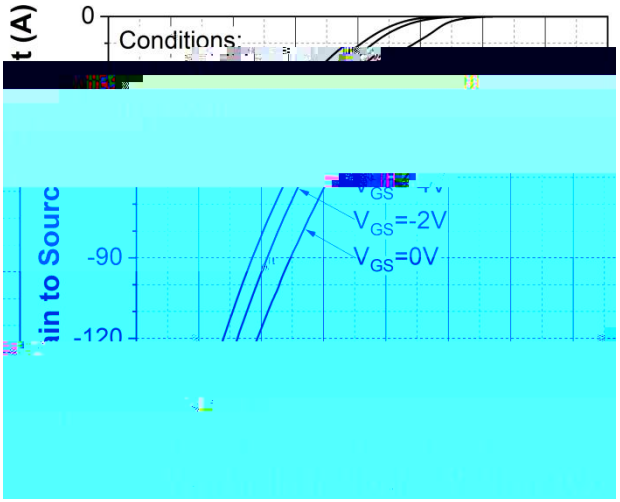

150
Conditions: V_{GS} = 18V

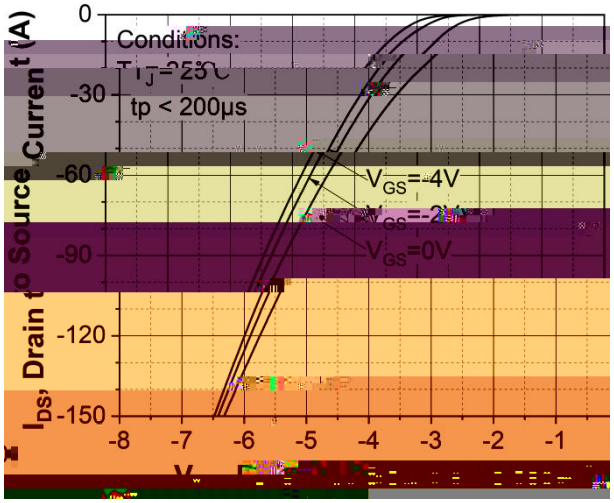

2.5
Conditions:
I_D = 32A
2.0
tp < 200μs
1.5
V_{GS} = 18V

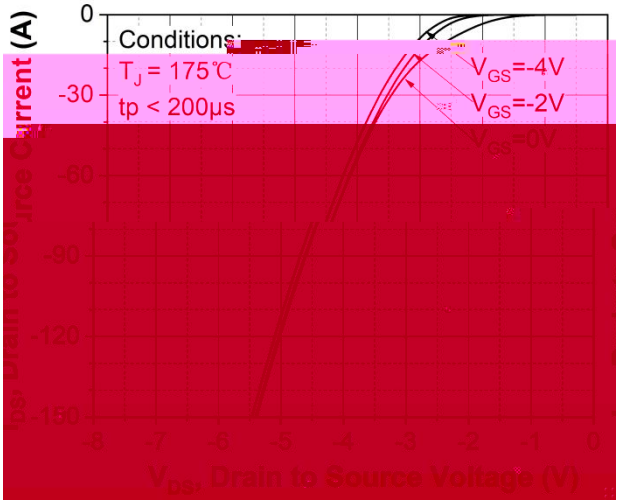

Conditions:
V_{GS} = 18V
tp < 200μs
90
T_J = 175℃
60
T_J = -55℃
30
T_J = 25℃
0
0
20
40
60
80

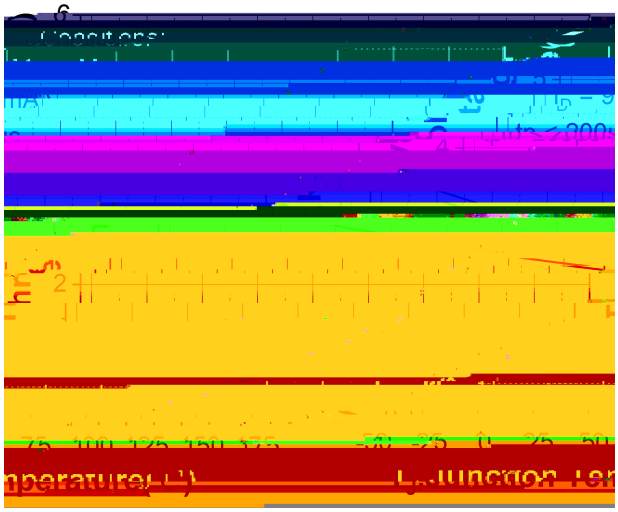

80
Conditions:

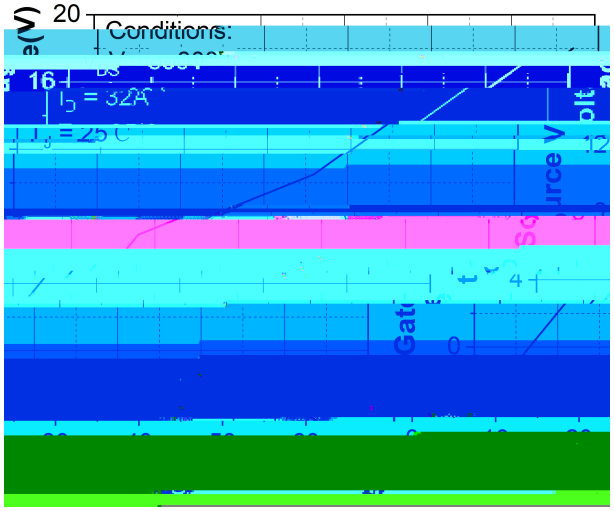

150
120
90
Conditions:
V_{DS} = 20V
tp < 200μs
T_J = -55℃

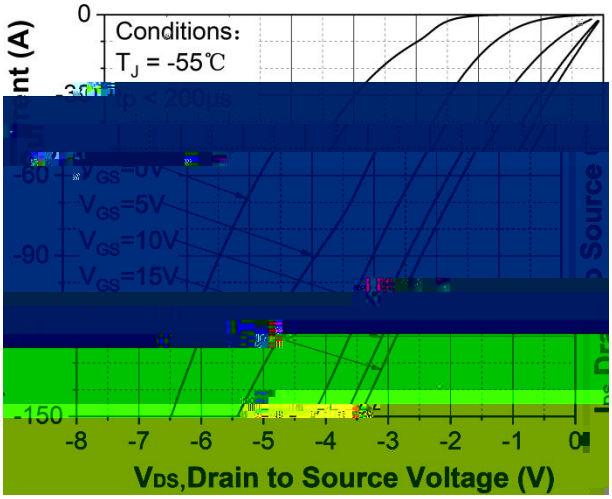

0
-90
-120
Conditions:
V_{GS}=-2V
V_{GS}=0V

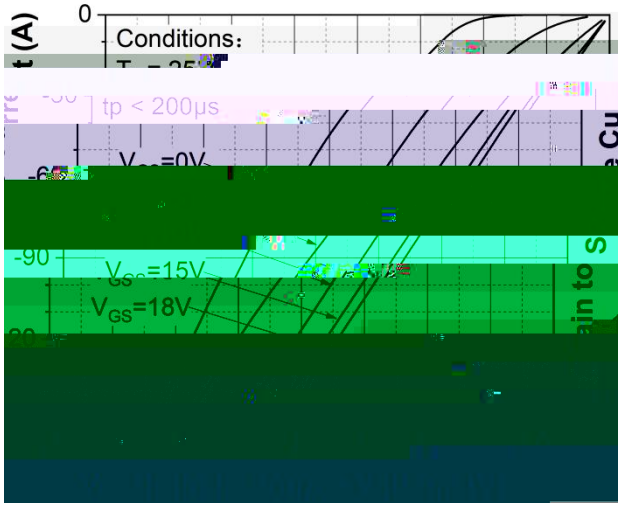

0
-30
-60
-90
-120
-150
-8
-7
-6
-5
-4
-3
-2
-1
Conditions:
tp < 200μs
V_{GS}=-4V
V_{GS}=0V
I_{DS}, Drain to Source Current (A)

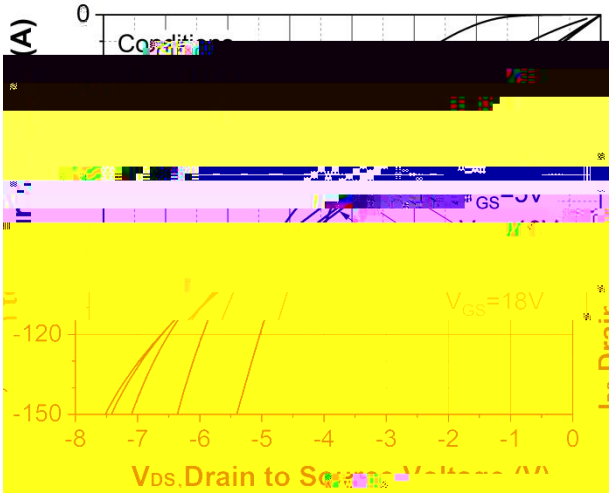

0
-30
-60
-90
-120
-150
Conditions:
T_J = 175℃
tp < 200μs
V_{GS}=-4V
V_{GS}=-2V
V_{GS}=0V
V_{DS}, Drain to Source Voltage (V)

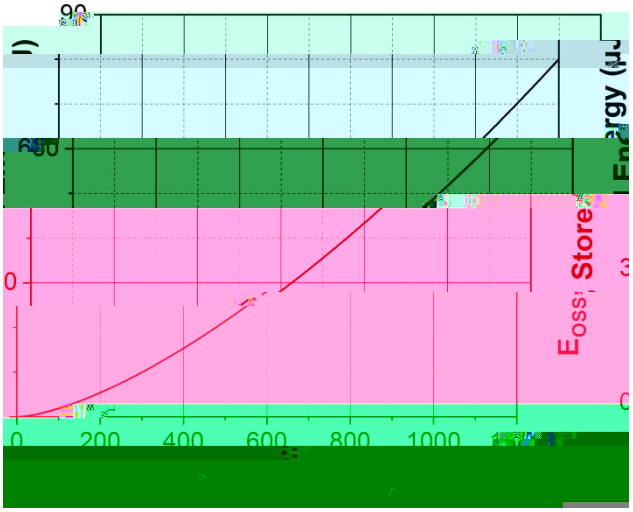


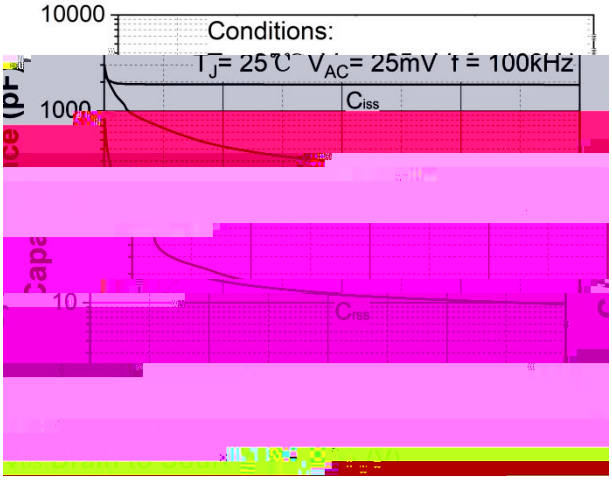

20
16
Conditions:

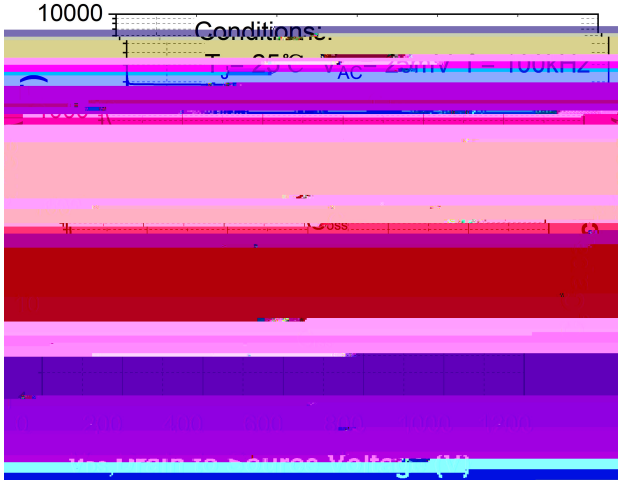

Conditions:
T_J = -55℃
tp < 200μs
V_{GS}=0V
V_{GS}=5V
V_{GS}=10V
V_{GS}=15V
0
-60
-90
-150
-8 -7 -6 -5 -4 -3 -2 -1 0
V_{DS},Drain to Source Voltage (V)

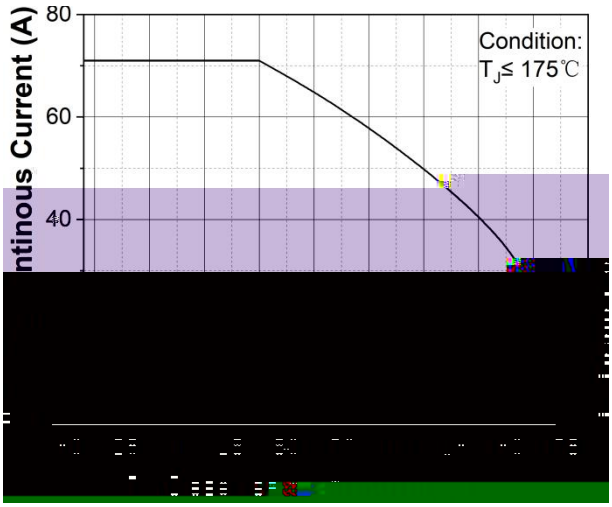

Conditions:
tp < 200μs
V_{GS}=0V
V_{GS}=15V
V_{GS}=18V
0
-90

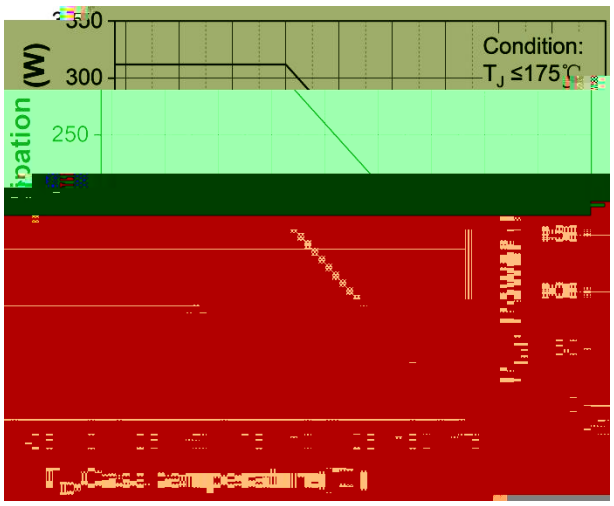

V_{GS}=18V
0
-120
-150
-8 -7 -6 -5 -4 -3 -2 -1 0

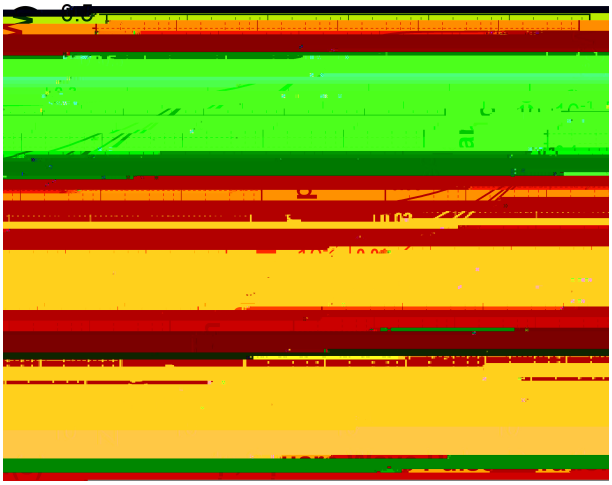

600
0
0 200 400 600 800 1000

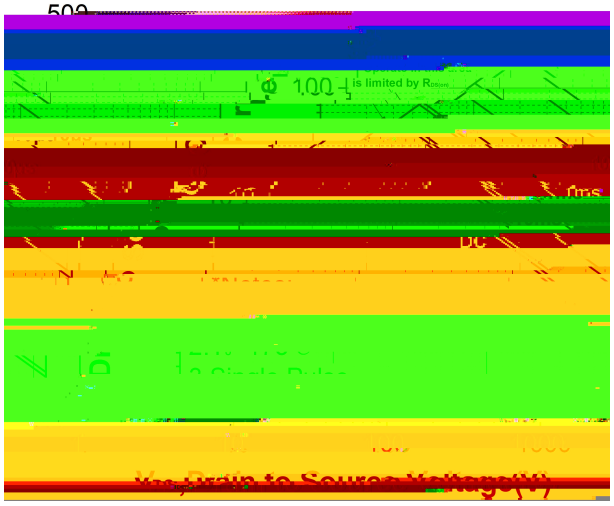

Conditions:
T_J= 25℃ V_{AC}= 25mV f = 100kHz
10000
1000
10
C_{iss}
C_{rss}

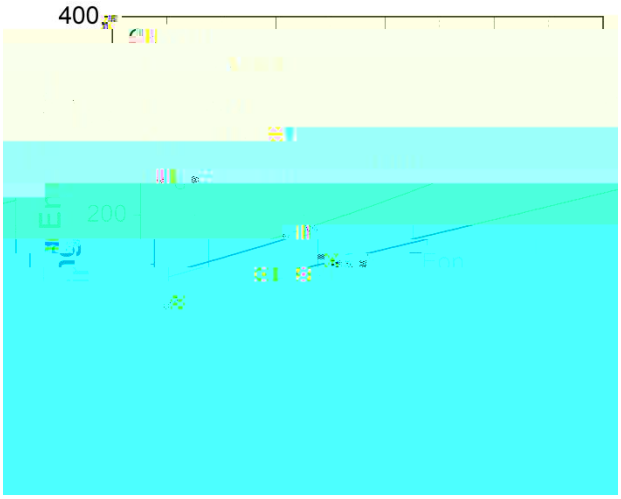

Conditions:
10000

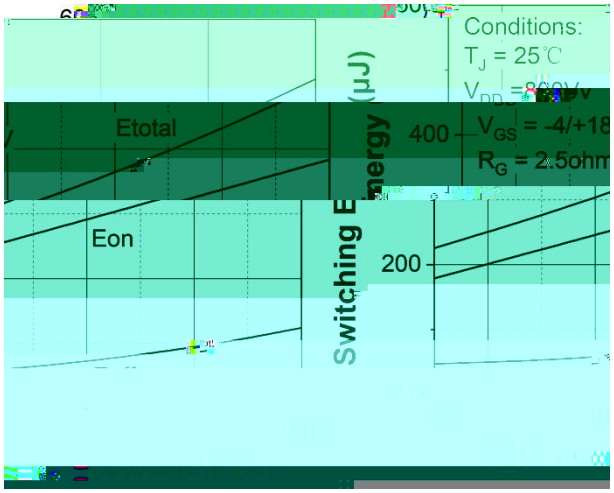

ntinous Current (A)
80
60
40
Condition:
$T_J \leq 175℃$

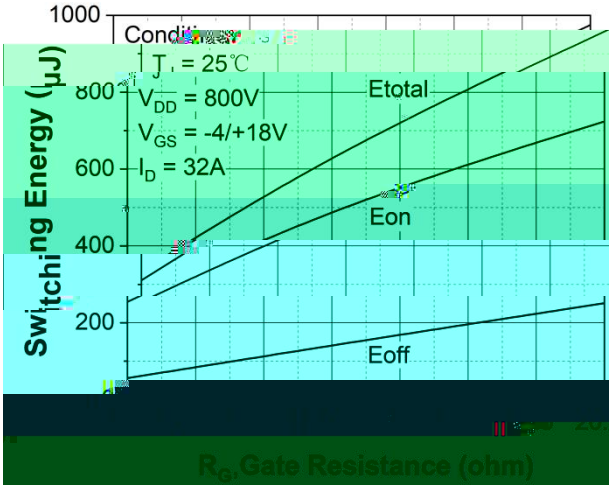

(W)
300
250
Condition:
$T_J \leq 175℃$

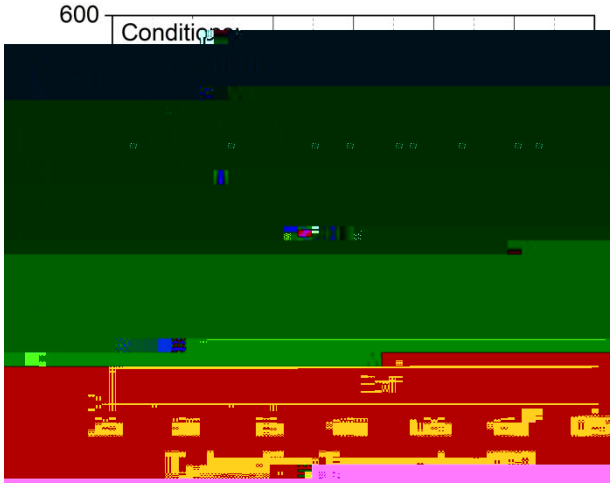


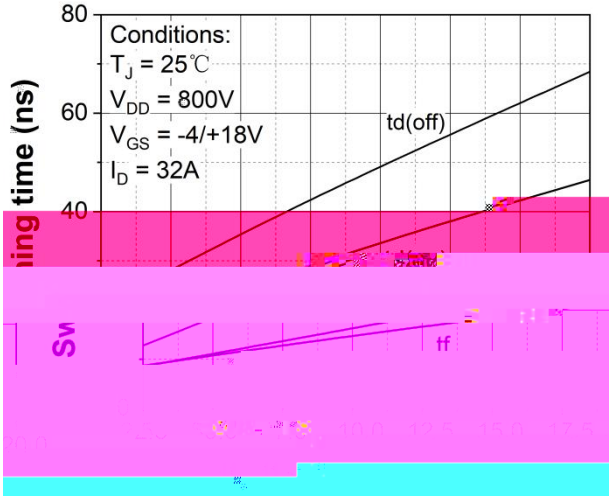

100 μs
is limited by R

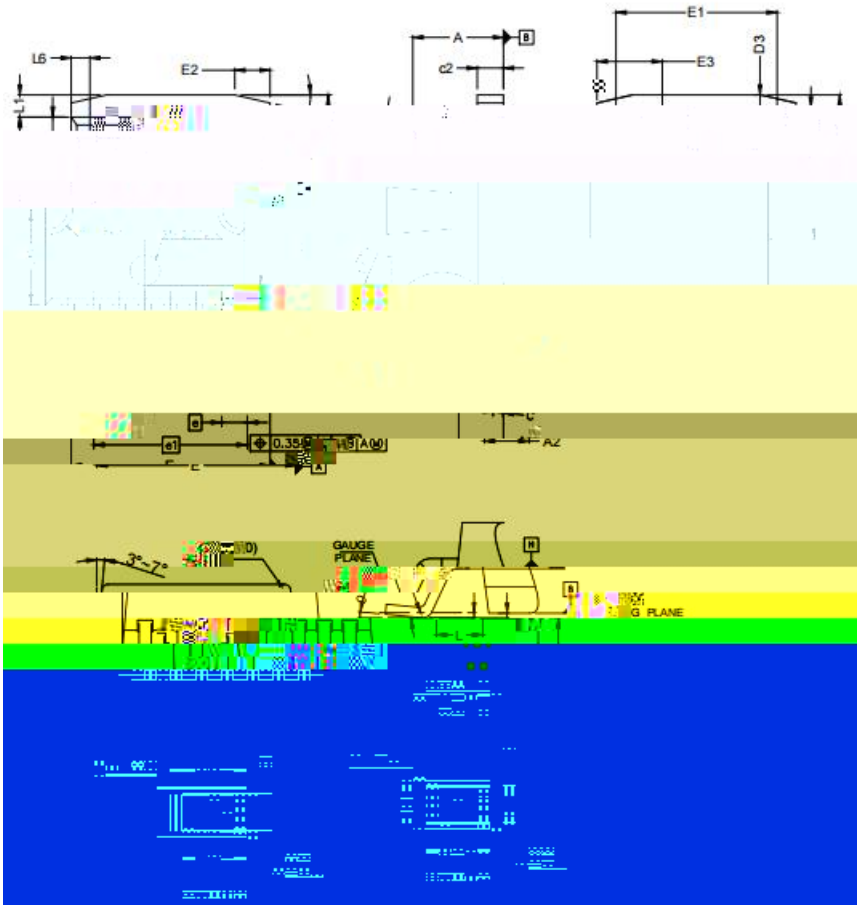

400
200


Conditions:
T_J = 25℃
V_{GS} = -4/+18
R_G = 2.5ohm
Etotal
Eon
400
200

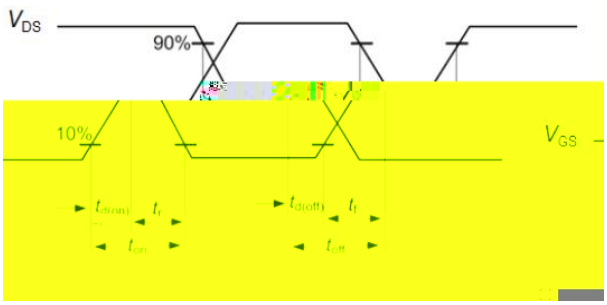

1000
800
600
400
200
Conditions:
T_J = 25℃
V_{DD} = 800V
V_{GS} = -4/+18V
I_D = 32A
Etotal
Eon
Eoff
Switching Energy (μJ)
R_G,Gate Resistance (ohm)

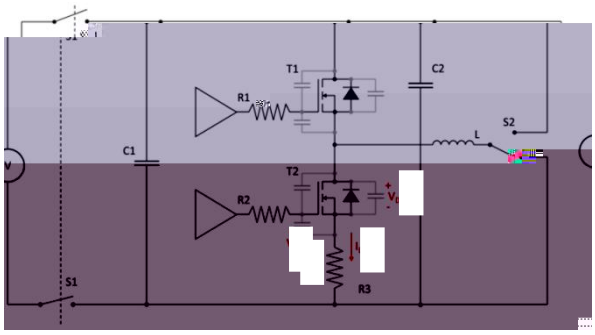

600
Conditions:

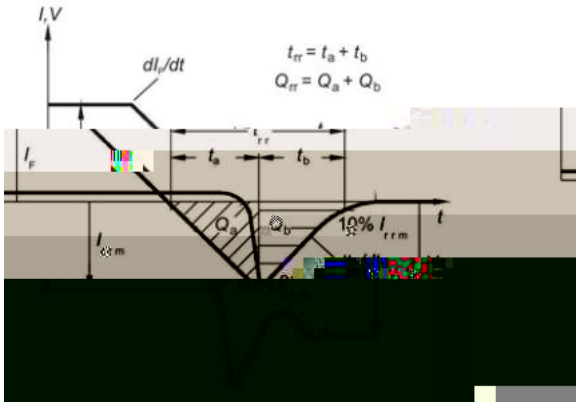

80
60
40
Conditions:
T_J = 25℃
V_{DD} = 800V
V_{GS} = -4/+18V
I_D = 32A
td(off)
ing time (ns)



SYMBOL	MIN	MAX	SYMBOL	MIN	MAX
A	4.30		L	1.78	2.79
A1		0.25			
				1.048SC	
	0.60	0.75	L6	0.93BSC	
	0.45	0.60	H	14.61	15.88
	0.45	0.55			


V_{DS}
90%
10%
V_{GS}
$t_{d(on)}$
t_r
t_{on}
$t_{d(off)}$
t_f
t_{off}


T1
C2
R1
S2
L
C1
T2
R2
R3
S1


I,V
dI_F/dt
$t_{rr} = t_a + t_b$
$Q_{rr} = Q_a + Q_b$
I_F
t_a
t_b
Q_a
Q_b
10% I_{rrm}
t

		——	——
		——	——
			——